

Supporting Information

Electrochemical Induced V_5S_8/V_2O_5 Heterostructures Manipulate Redox Kinetics for Aqueous Zinc-Ion Batteries

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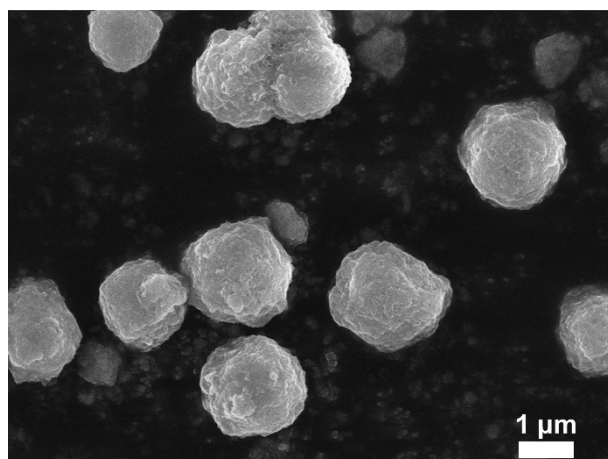


Figure S1. SEM image of VS₄.

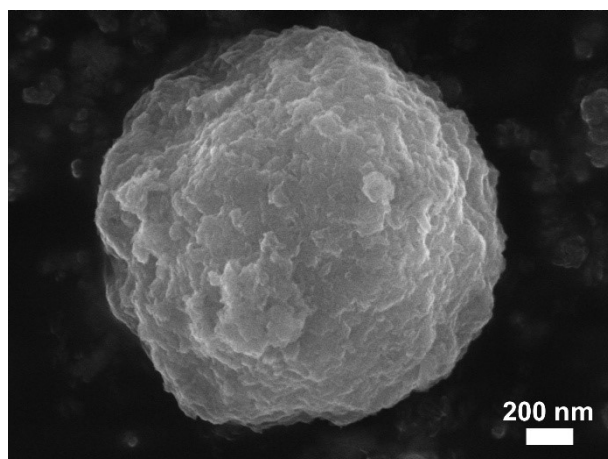


Figure S2. SEM image of VS₄.

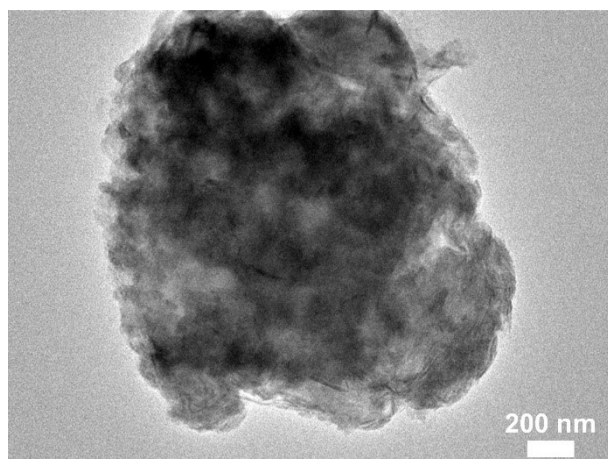


Figure S3. TEM image of VS₄.

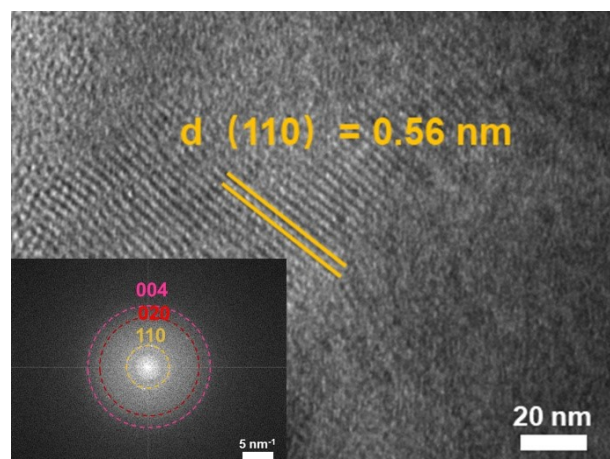


Figure S4. HRTEM image with corresponding SAED pattern of VS_4 .

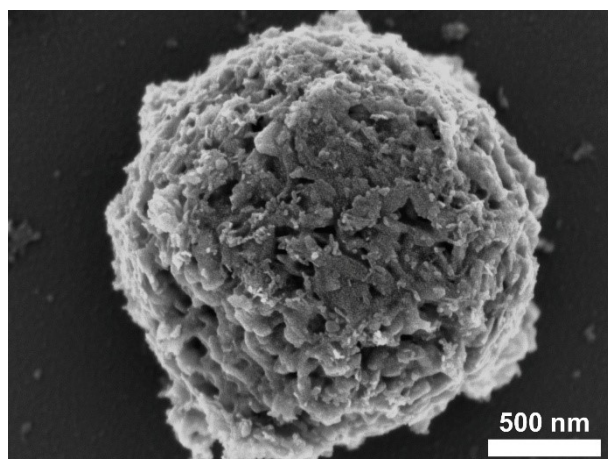


Figure S5. SEM image of V_5S_8 .

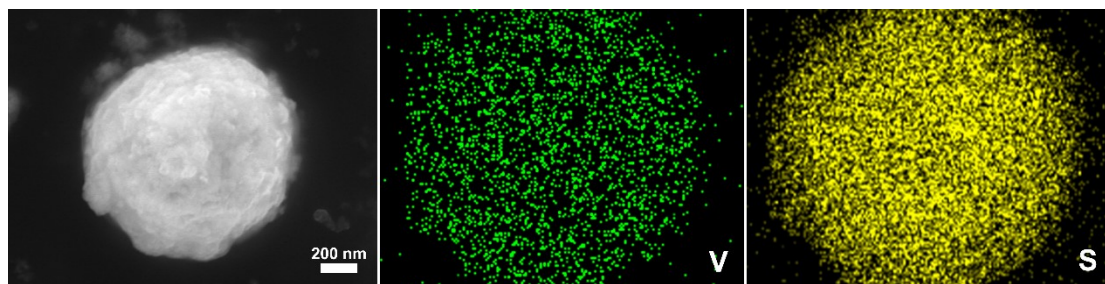


Figure S6. Element mapping of VS_4 .

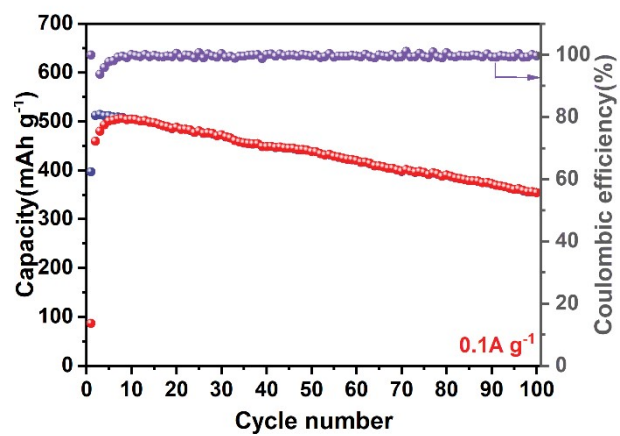


Figure S7. Cycling performance of V_5S_8 at 0.1 A g^{-1} .

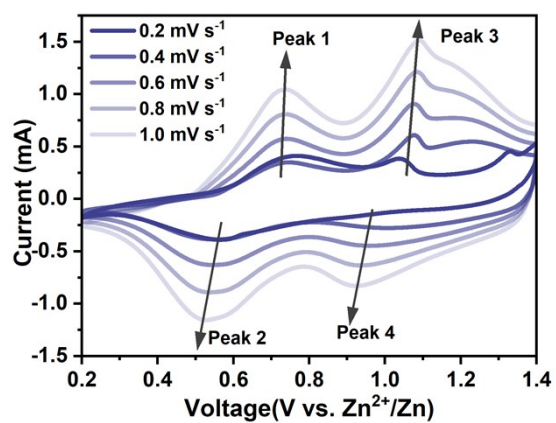


Figure S8. Cyclic voltammograms curves of V_5S_8 at various scan rates.

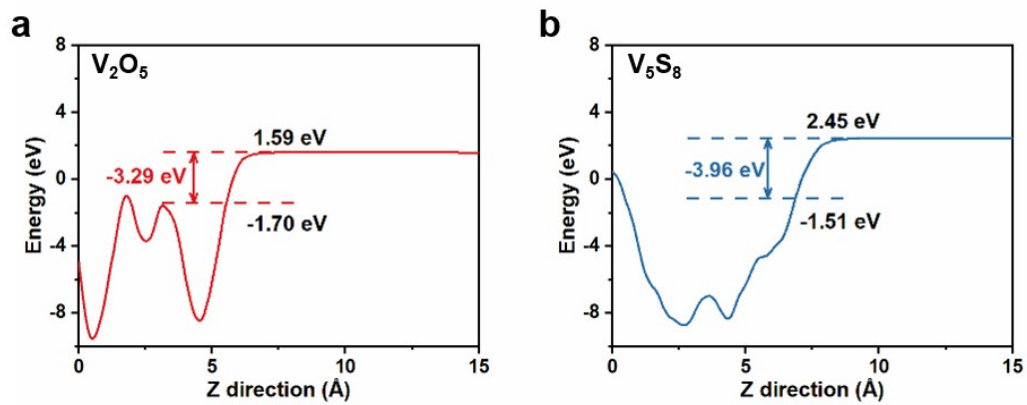


Figure S9. Surface potential of (a) V_2O_5 and (b) V_5S_8 .

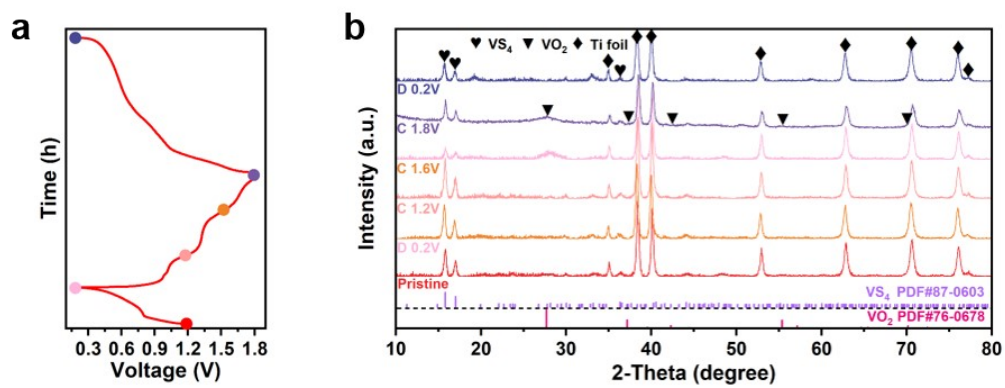


Figure S10. a) Galvanostatic charge and discharge curves of VS₄ at 0.1 A g⁻¹. b) Ex-situ XRD patterns of the VS₄ electrode at different state of charge.

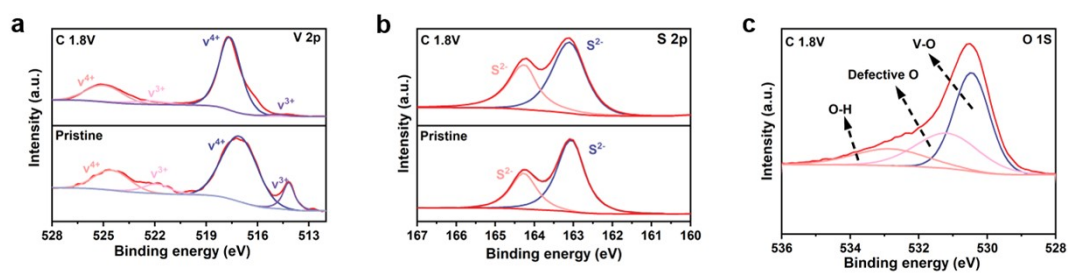


Figure S11. High-resolution XPS spectra of a) V 2p, b) S 2p, and c) O 1s of the VS₄ electrode at different state of charge.

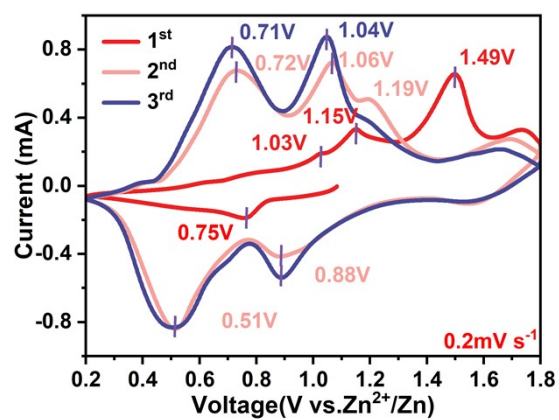


Figure S12. Cyclic voltammograms curves of VS₄/VO₂ heterostructure at 0.2 mV s⁻¹.

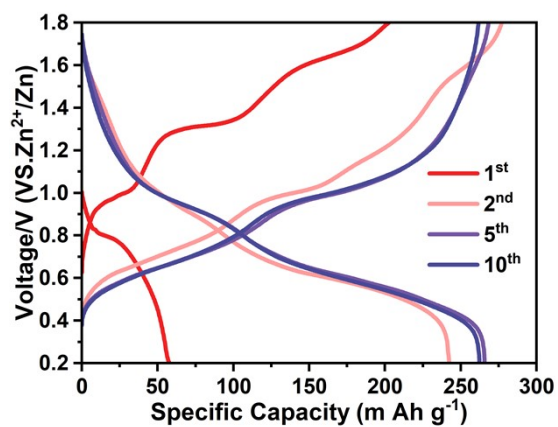


Figure S13. Galvanostatic charge and discharge curves of VS₄/VO₂ heterostructure at 0.1 A g⁻¹.

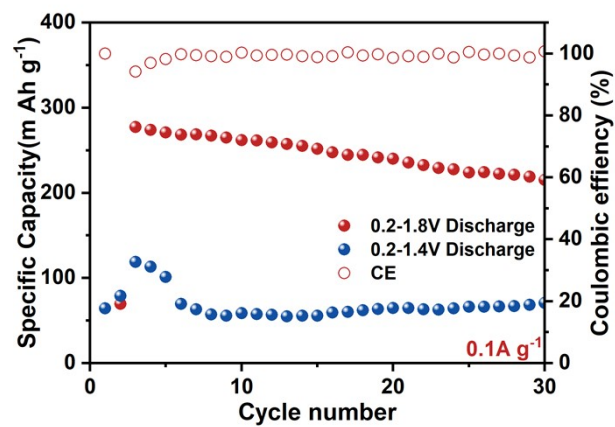


Figure S14. Comparison of cycling performance of VS₄/VO₂ heterostructure and

VS₄.

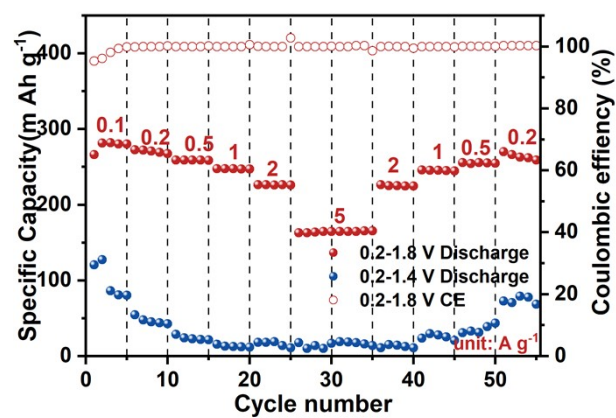


Figure S15. Comparison of rate capability of VS₄/VO₂ heterostructure and VS₄ at various current densities.

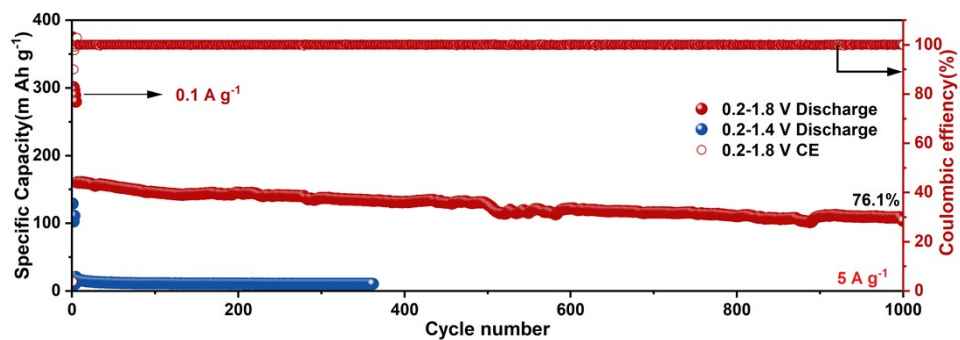


Figure S16. Comparison of long-term cycling performance of VS₄/VO₂ heterostructure and VS₄.

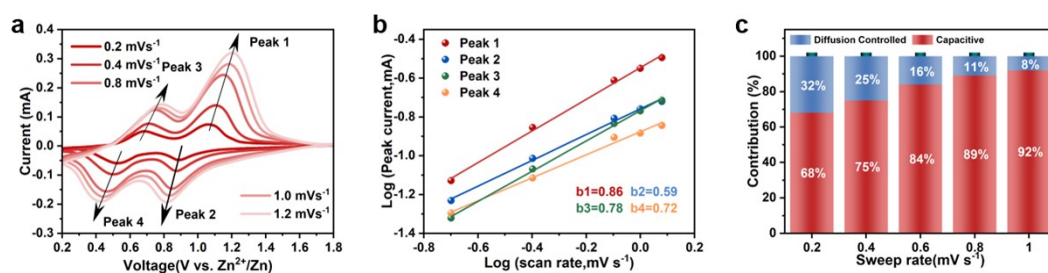


Figure S17. a) Cyclic voltammograms curves of VS₄/VO₂ heterostructure at various scan rates. b) The *b*-values of VS₄/VO₂ heterostructure. c) Capacity contribution of VS₄/VO₂ heterostructure at different scan rates.

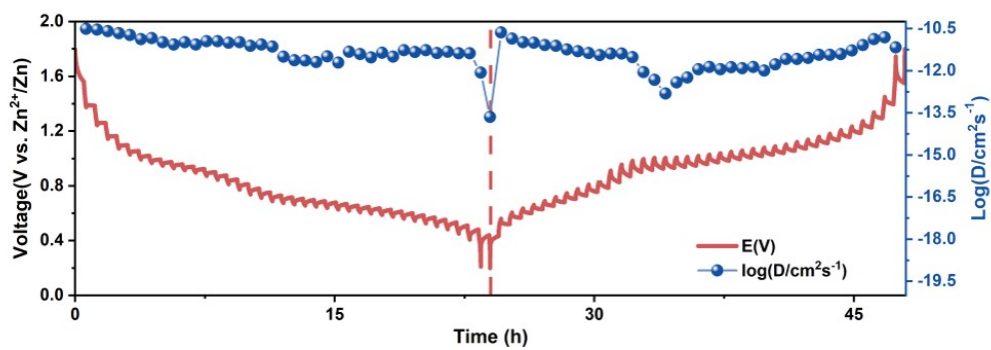


Figure S18. Galvanostatic charge and discharge curves at 0.1 A g⁻¹ of galvanostatic intermittent titration technique and Zn²⁺ ions diffusion coefficient of VS₄/VO₂ heterostructure.

Table S1. Comparison of electrochemical performances of the V_5S_8/V_2O_5 heterostructure with reported cathode materials for Zn^{2+} ions storage.

Material	Current density (A g ⁻¹)	Specific capacity (mAh g ⁻¹)	Cycle number	capacity retention rate	Reference
VS ₂	0.1	170	25	77%	[1]
VS ₂ @VOOH	0.5	143	200	83%	[2]
VS ₂ /VO _x	0.05	310	70	75%	[3]
VS ₄	1	219	100	57.2	[4]
VS ₄ /rGO	1	296	100	80%	[4]
Oxygen-incorporated MoS ₂	0.1	232	/	68%	[5]
VS ₂	0.5	165	500	83%	[6]
V₅S₈/V₂O₅ heterostructure	0.1	352	100	81%	This work

Table S2. Comparison of diffusion coefficient of the V_5S_8/V_2O_5 heterostructure with previous reported cathode materials.

Cathode Material	Diffusion coefficient [cm ² s ⁻¹]	Ref.
VS ₂	10 ⁻⁹ -10 ⁻¹⁰	[7]
W doped VS ₄	10 ⁻¹²	[8]
Mo doped VS ₄	10 ⁻¹²	[9]
VS ₄	10 ⁻¹¹ -10 ⁻¹³	[10]
V ₆ O ₁₃ •10H ₂ O	10 ⁻¹⁰ -10 ⁻¹²	[11]
V₅S₈/V₂O₅ heterostructure	10⁻¹⁰-10⁻¹²	This work

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